NXPs General Purpose Airfast GaN Transistor

5/26/2021 – San Jose, California: RFMW announces design and sales support for a versatile, GaN on SiC discrete transistor. NXP’s A3G26D055NT4 RF transistor delivers 55 Watts of peak power from 100 to 2690 MHz for applications ranging from cellular infrastructure and RF energy to wideband communications including 5G mMIMO radios. Operating from a 48V supply, the A3G26D055NT4 has a pre-matched RF input and boasts 50% efficiency and >13 dB of gain. The higher power density of GaN on SiC enables a high output impedance, making devices easier to match across the device bandwidth and ensuring a cooler channel temperature for higher reliability.

Samples are available for qualified requirements through RFMW at 1-877-FOR RFMW (367-7369) within North America; or please find your local sales engineer (worldwide) at the contact page on the RFMW web site.

About RFMW

RFMW is a specialty electronics distribution company focused exclusively on serving customers that require RF and microwave components and semiconductors, as well as component engineering support. The company continues to expand its list of products from selective suppliers with RF/microwave expertise. RFMW deploys a highly experienced, technically skilled team to assist customers with component selection and fulfillment.

To learn more about RFMW, visit their Website at www.rfmw.com, or call us at 1.877.FOR.RFMW (367-7369), or via e-mail at info@rfmw.com.

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